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# 1N5719, 1N5767, 5082-3001, 5082-3039, <br> 5082-3077, 5082-3080/81,5082-3188, 5082-3379 

## Data Sheet

## Description/Applications

These general purpose switching diodes are intended for low power switching applications such as RF duplexers, antenna switching matrices, digital phase shifters, and time multiplex filters. The 5082-3188 is optimized for VHF/UHF bandswitching.

The RF resistance of a PIN diode is a function of the current flowing in the diode. These current controlled resistors are specified for use in control applications such as variable RF attenuators, automatic gain control circuits, RF modulators, electrically tuned filters, analog phase shifters, and RF limiters.

Outline 15 diodes are available on tape and reel. The tape and reel specification is patterned after RS-296-D.
Maximum RatingsJunction Operating andStorage Temperature Range$-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$
Power Dissipation $25^{\circ} \mathrm{C}$ ..... 250 mW
(Derate linearly to zero at $150^{\circ} \mathrm{C}$ )
Peak Inverse Voltage (PIV)

$\qquad$
same as $\mathrm{V}_{\mathrm{BR}}$ Maximum Soldering Temperature $260^{\circ} \mathrm{C}$ for 5 sec

## Features

- Low Harmonic Distortion
- Large Dynamic Range
- Low Series Resistance
- Low Capacitance


## Outline 15



DIMENSIONS IN MILLIMETERS AND (INCHES)

## Mechanical Specifications

The Avago Outline 15 package has a glass hermetic seal with dumet leads. The lead finish is 95-5 tin-lead (SnPb) for all PIN diodes. The leads on the Outline 15 package should be restricted sothat the bendstarts at least $1 / 16$ inch ( 1.6 mm )
from the glass body. Typical package inductance and capacitance are 2.5 nH and 0.13 pF , respectively. Marking is by digital coding with a cathode band.

## General Purpose Diodes

Electrical Specifications at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$

| Part <br> Number <br> $\mathbf{5 0 8 2 -}$ | Maximum <br> Total <br> Capacitance <br> $\mathbf{C}_{\mathrm{T}}(\mathbf{p F})$ | Minimum <br> Breakdown <br> Voltage <br> $\mathbf{V}_{\mathrm{BR}}(\mathbf{V})$ | Maximum <br> Residual Series <br> Resistance <br> $\mathbf{R}_{\mathrm{s}}(\Omega)$ | Effective Carrier <br> Lifetime <br> $\tau(\mathbf{n s})$ | Reverse Recovery <br> Time <br> $\mathbf{t}_{\mathrm{m}}$ (ns) |
| :---: | :---: | :---: | :---: | :---: | :---: |
| General Purpose Switching and Attenuating <br> 3001 |  | 0.25 | 200 | 1.0 | 100 (min.) |

## Notes:

Typical CW power switching capability for a shunt switch in a $50 \Omega$ system is 2.5 W .

## RF Current Controlled Resistor Diodes

## Electrical Specifications at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$

| Part Number | Effective <br> Carrier <br> Lifetime <br> $\tau$ (ns) | Min. Breakdown Voltage $V_{B R}(V)$ | Max. Residual Series Resistance $\mathrm{R}_{5}(\Omega)$ | Max. <br> Total Capacitance $C_{T}(\mathrm{pF})$ | High Resistance Limit, $\mathrm{R}_{\mathrm{H}}(\Omega)$ |  | Low Resistance Limit, $\mathbf{R}_{\mathbf{L}}(\Omega)$ |  | Max. Difference in Resistance vs. Bias Slope, Dc |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | Min. | Max. | Min. | Max. |  |
| 5082-3080 | 1300 (typ.) | 100 | 2.5 | 0.4 | 1000 |  |  | 8** |  |
| 1N5767* | 1300 (typ.) | 100 | 2.5 | 0.4 | 1000 |  |  | 8** |  |
| 5082-3379 | 1300 (typ.) | 50 |  | 0.4 |  |  |  | 8** |  |
| 5082-3081 | 2500 (typ.) | 100 | 3.5 | 0.4 | 1500 |  |  | 8** |  |
| Test Conditions | $\begin{gathered} I_{F}=50 \mathrm{~mA} \\ I_{R}=250 \mathrm{~mA} \end{gathered}$ | $V_{R}=V_{B R^{\prime}}$ <br> Measure $\mathrm{I}_{\mathrm{R}} \leq 10 \mu \mathrm{~A}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA} \\ & \mathrm{f}=100 \mathrm{MHz} \end{aligned}$ | $\begin{gathered} V_{R}=50 \mathrm{~V} \\ \mathrm{f}=1 \mathrm{MHz} \end{gathered}$ | $\begin{aligned} & I_{F}=0 . \\ & f=10 \end{aligned}$ | $\begin{aligned} & 1 \mathrm{~mA} \\ & \mathrm{MHz} \end{aligned}$ | $\begin{aligned} & I_{F}=1 . \\ & I_{F}=20 \\ & f=10 \end{aligned}$ | $\begin{aligned} & 0 \mathrm{~mA} \\ & \mathrm{~mA} \mathrm{~A}^{* *} \\ & \mathrm{MHz} \end{aligned}$ | Batch <br> Matched at $\mathrm{I}_{\mathrm{F}}=0.01 \mathrm{~mA}$ and 1.0 mA $\mathrm{f}=100 \mathrm{MHz}$ |

*The 1 N5767 has the additional specifications: $\tau=1.0 \mathrm{msec}$ minimum
$\mathrm{I}_{\mathrm{R}}=1 \mu \mathrm{~A}$ maximum at $\mathrm{V}_{\mathrm{R}}=50 \mathrm{~V}$
$\mathrm{~V}_{\mathrm{F}}=1 \mathrm{~V}$ maximum at $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$.

## Typical Parameters at $\mathrm{T}_{\mathrm{A}}=\mathbf{2 5 ^ { \circ }}$ ( unless otherwise noted)



Figure 1. Forward Current vs. Forward Voltage.


Figure 4. Typical Capacitance vs. Reverse Voltage.


Figure 7. Typical Second Order Intermodulation Distortion.


Figure 2. Typical RF Resistance vs. Forward Bias Current.


Figure 5. Typical Capacitance vs. Reverse Voltage.


Figure 8. Typical Cross Intermodulation Distortion.


Figure 3. Typical RF Resistance vs. Forward Bias Current.


Figure 6. Typical Reverse Recovery Time vs. Forward Current for Various Reverse Driving Voltages.

## Diode Package Marking

1N5xxx 5082-xxxx
would be marked:

| 1 Nx | xx |
| :--- | :--- |
| $x x x$ | $x x$ |
| YWW | YWW |

where xxxx are the last four digits of the 1Nxxxx or the 5082-xxxx part number. Y is the last digit of the calendar year. WW is the work week of manufacture.

Examples of diodes manufactured during workweek 45 of 1999:

| 1N5712 | $5082-3080$ |
| :--- | :--- |
| would be marked: |  |
| 1N5 | 30 |
| 712 | 80 |
| 945 | 945 |

## Part Number Ordering Information

| Part Number | No. of devices | Container |
| :--- | :--- | :--- |
| 5082-3xxx\#T25/1N57xx\#T25 | 2500 | Tape \& Reel |
| 5082-3xxx\#T50/ 1N57xx\#T50 | 5000 | Tape \& Reel |
| 5082-3xxx/ 1N57xx | 100 | Antistatic bag |

